

**LISTING OF THE CLAIMS:**

Claims 1-56 (Canceled)

57. (Original) A dual workfunction high-performance support MOSFET/EDRAM array comprising at least one support region having a local interconnect formed therein and at least one array region having at least one wordline formed therein, said at least one array region and said at least one support region are separated by an isolation region, and said at least one wordline and said local interconnect are comprised of identical material.

58. (Original) The dual workfunction high-performance support MOSFET/EDRAM array of Claim 57 wherein said at least one array region includes a plurality of DRAM cells embedded in a semiconductor substrate.

59. (Original) The dual workfunction high-performance support MOSFET/EDRAM array of Claim 58 wherein said DRAM cells are vertical DRAMs.

60. (Newly added) The dual workfunction high-performance support MOSFET/EDRAM array of Claim 57 wherein said identical material of at least one wordline and said local interconnect comprises a W/WN stack.

61. (Newly added) The dual workfunction high performance support MOSFET/EDRAM array of Claim 57, wherein said at least one wordline and said local interconnect comprise a SiN cap.

62. (Newly added) The dual workfunction high-performance support MOSFET/EDRAM of Claim 57, wherein said identical material of said wordline and said local interconnect comprises an identically layered stack having top surfaces which are approximately co-planar.